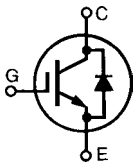
IXYS

HiPerFAST™ IGBT with Diode

Light Speed Series

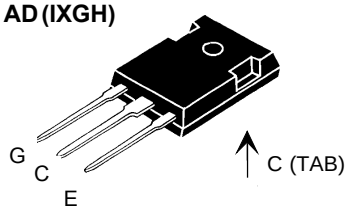
IXGH 32N60CD1
IXGT 32N60CD1

V_{CES} = 600 V
I_{C25} = 60 A
$V_{CE(SAT)typ}$ = 2.1 V
$t_{fi(typ)}$ = 55 ns

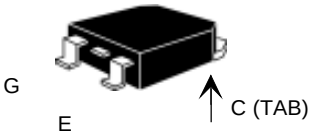


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	600	V
V_{CGR}	T_J = 25°C to 150°C; R_{GE} = 1 MΩ	600	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C	60	A
I_{C90}	T_C = 90°C	32	A
I_{CM}	T_C = 25°C, 1 ms	120	A
SSOA (RBSOA)	V_{GE} = 15 V, T_{VJ} = 125°C, R_G = 10 Ω Clamped inductive load @ 0.8 V_{CES}	I_{CM} = 64	A
P_C	T_C = 25°C	200	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
Maximum Lead and Tab temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	°C
M_d	Mounting torque, TO-247 AD	1.13/10	Nm/lb.in.
Weight	TO-247 AD	6	g
	TO-268	5	g

TO-247 AD (IXGH)



TO-268 (D3) (IXGT)



G = Gate C = Collector
E = Emitter

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
BV_{CES}	I_C = 250∝A, V_{GE} = 0 V		600			V
$V_{GE(th)}$	I_C = 250 ∝A, V_{CE} = V_{GE}		2.5		5.0	V
I_{CES}	V_{CE} = 0.8 • V_{CES}	T_J = 25°C			200	∝A
	V_{GE} = 0 V	T_J = 125°C			3	mA
I_{GES}	V_{CE} = 0 V, V_{GE} = ±20 V				±100	nA
$V_{CE(sat)}$	I_C = I_{C90}, V_{GE} = 15 V			2.1	2.5	V

Features
- International standard TO-247AD package
- High current handling capability
- Latest generation HDMOS™ process
- MOS Gate turn-on
  - drive simplicity

Applications
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

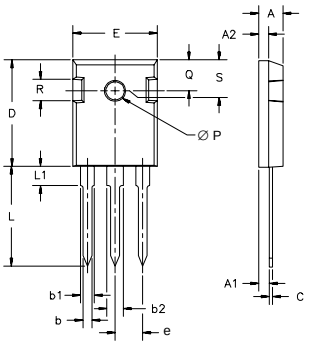
Advantages
- High power density
- Very fast switching speeds for high frequency applications
- High power surface mountable package

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
g_{fs}	$I_C = I_{C90}$; V_{CE} = 10 V, Pulse test, t ≤ 300 ∝s, duty cycle ≤ 2 %		25		S
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		2700		pF
C_{oes}			240		pF
C_{res}			50		pF
Q_g	$I_C = I_{C90}$, V_{GE} = 15 V, V_{CE} = 0.5 V_{CES}		110		nC
Q_{ge}			22		nC
Q_{gc}			40		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		25		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V		20		ns
$t_{d(off)}$	V_{CE} = 0.8 V_{CES}, $R_G = R_{off}$ = 4.7 Ω		85		ns
t_{fi}	Remarks: Switching times may increase for V_{CE} (Clamp) > 0.8 • V_{CES}, higher T_J or increased R_G		55		ns
E_{off}			0.32		mJ
$t_{d(on)}$	**Inductive load, T_J = 125°C**		25		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V		25		ns
E_{on}	V_{CE} = 0.8 V_{CES}, $R_G = R_{off}$ = 4.7 Ω		1		mJ
$t_{d(off)}$	Remarks: Switching times may increase for V_{CE} (Clamp) > 0.8 • V_{CES}, higher T_J or increased R_G		110	170	ns
t_{fi}			100	160	ns
E_{off}			0.85	1.25	mJ
R_{thJC}				0.62	K/W
R_{thCK}			0.25		K/W

Reverse Diode (FRED)

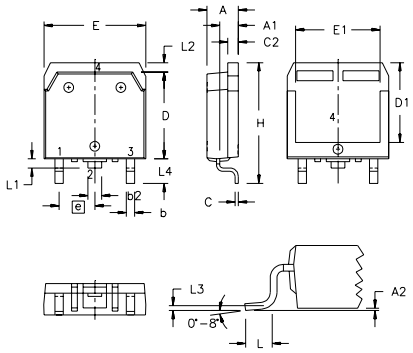
Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
V_F	$I_F = I_{C90}$, V_{GE} = 0 V, Pulse test, t ≤ 300 ∝s, duty cycle d ≤ 2 %	T_J = 150°C		1.6	V
		T_J = 25°C		2.5	V
I_{RM}	$I_F = I_{C90}$, V_{GE} = 0 V, -di_F/dt = 100 A/∝s		6		A
t_{rr}	V_R = 100 V	T_J = 100°C	100		ns
	I_F = 1 A; -di/dt = 100 A/∝s; V_R = 30 V	T_J = 25°C	25		ns
R_{thJC}				0.9	K/W

TO-247 AD Outline



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

TO-268 Outline



Terminals: 1 - Gate 2 - Collector
3 - Emitter

SYM	INCHES MIN	MAX	MILLIMETERS MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

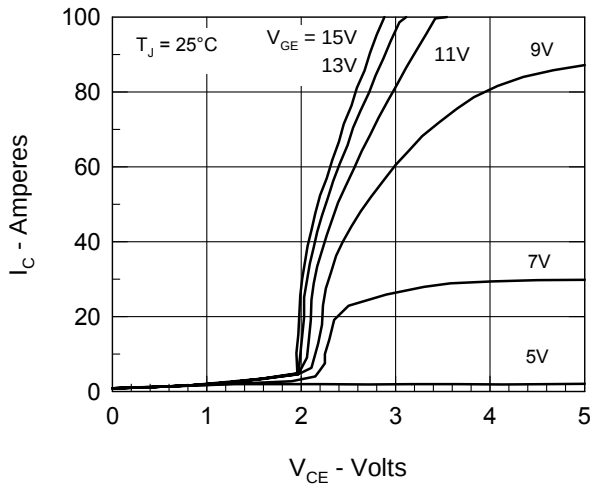


Fig. 1. Output Characteristics

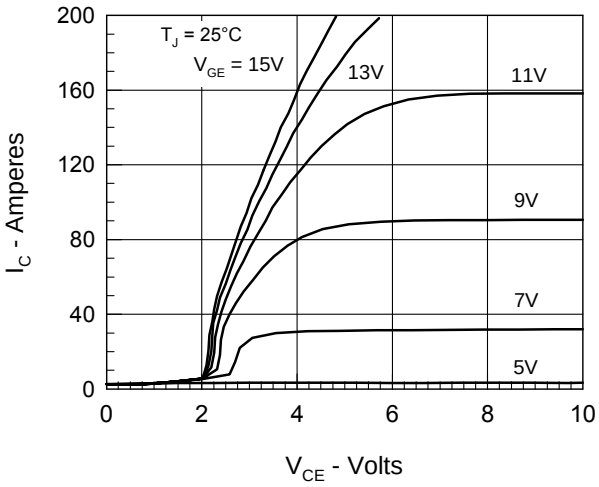


Fig. 2. Extended Output Characteristics

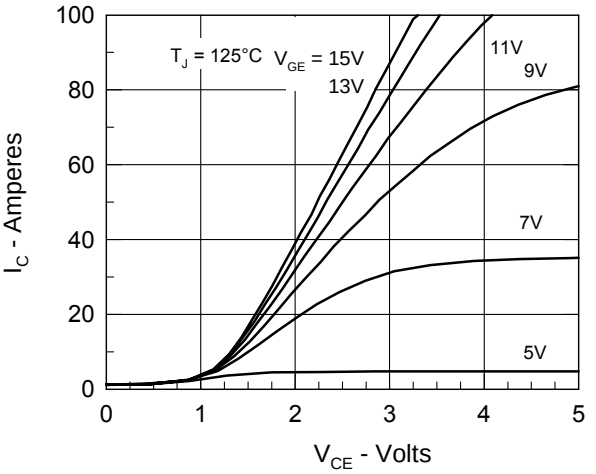


Fig. 3. High Temperature Output Characteristics

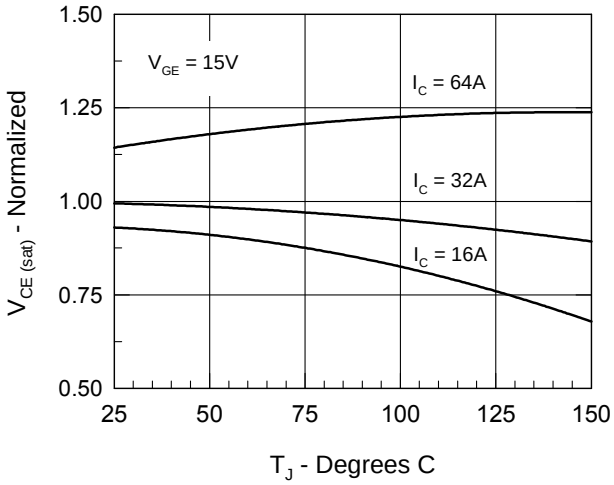


Fig. 4. Temperature Dependence of $V_{CE(sat)}$

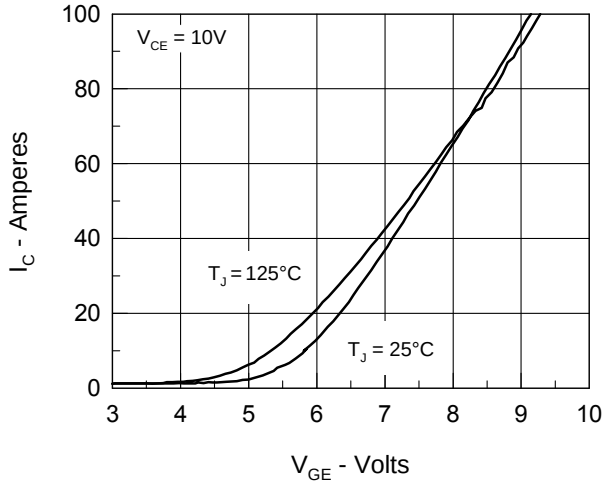


Fig. 5. Admittance Curves

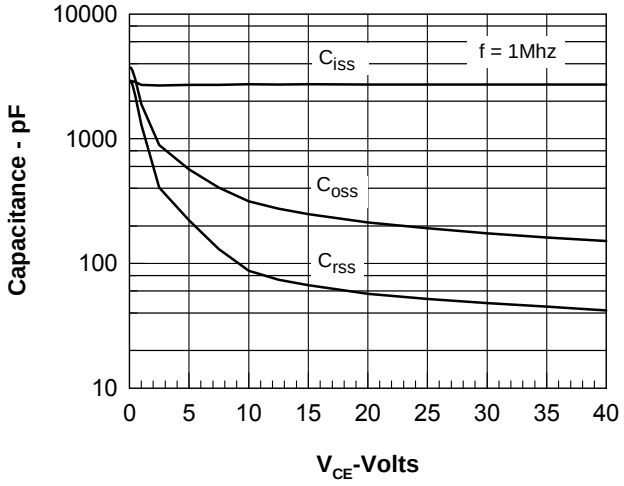


Fig. 6. Capacitance Curves

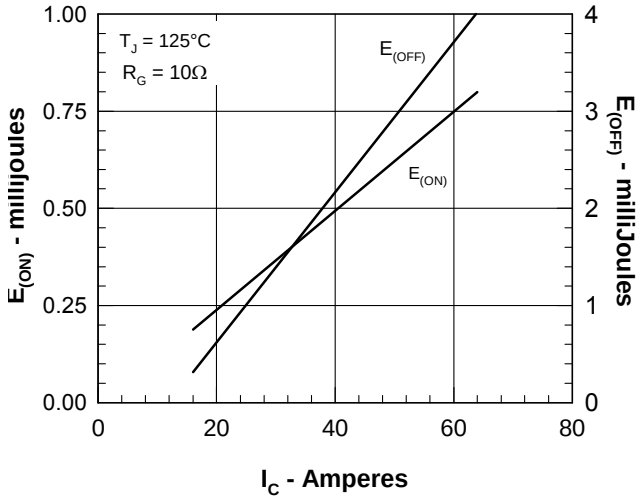


Fig. 7. Dependence of E_{ON} and E_{OFF} on I_C.

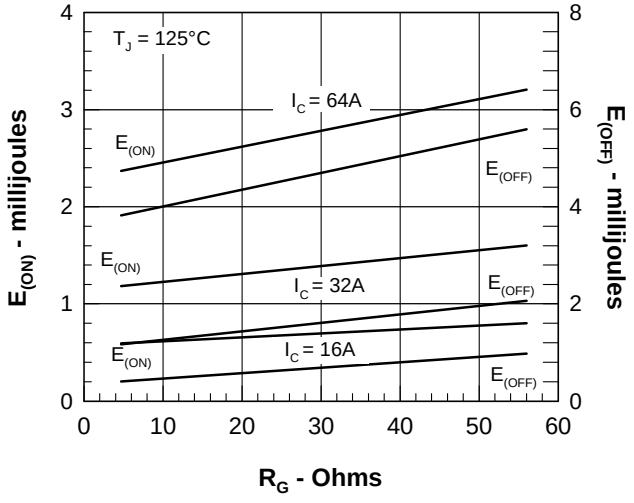


Fig. 8. Dependence of E_{ON} and E_{OFF} on R_G.

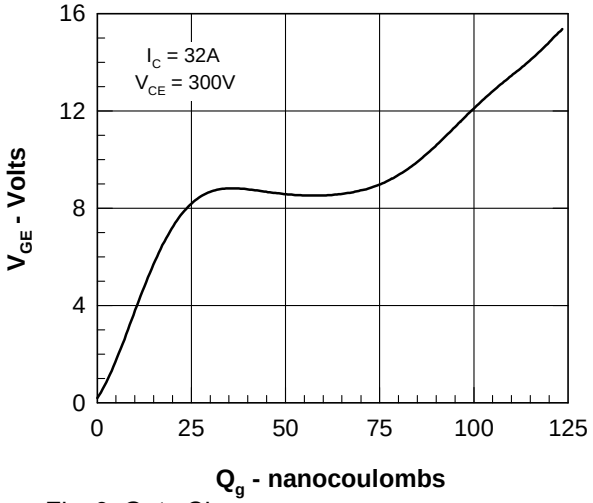


Fig. 9. Gate Charge

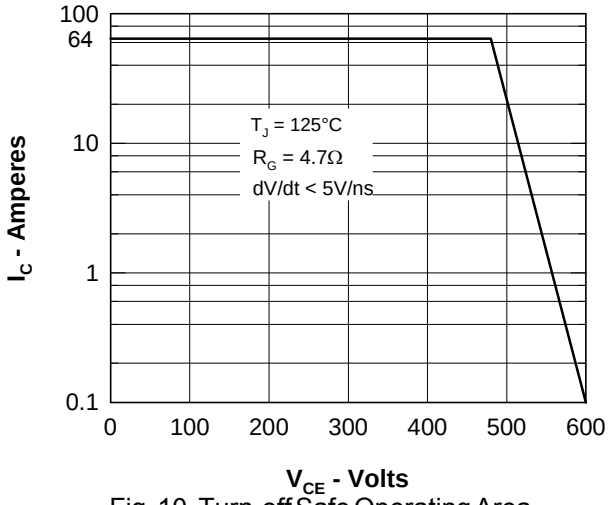


Fig. 10. Turn-off Safe Operating Area

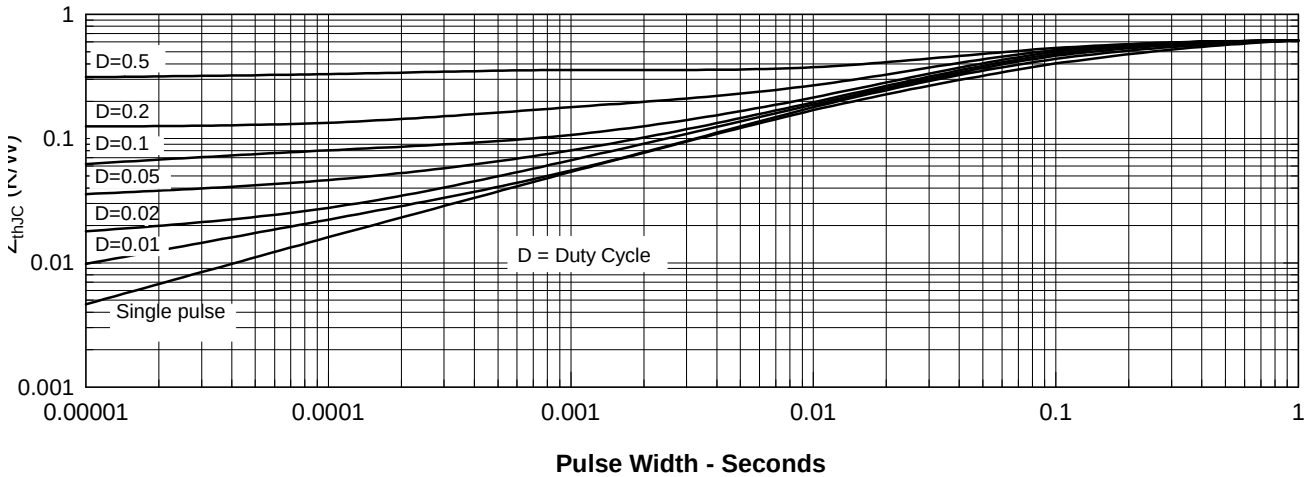


Fig. 11. Transient Thermal Resistance

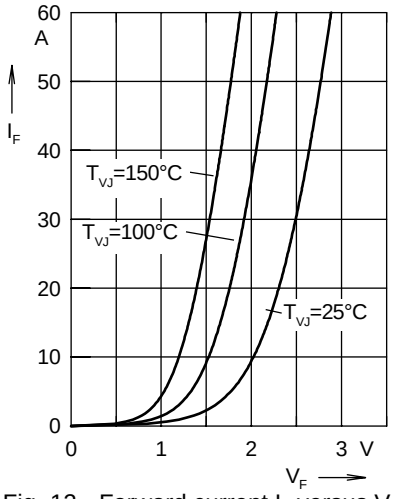


Fig. 12 Forward current I_F versus V_F

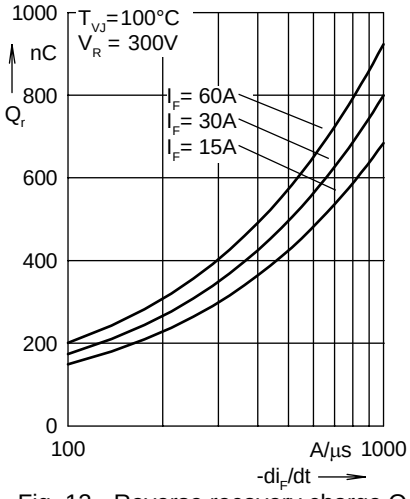


Fig. 13 Reverse recovery charge Q_r versus $-di_F/dt$

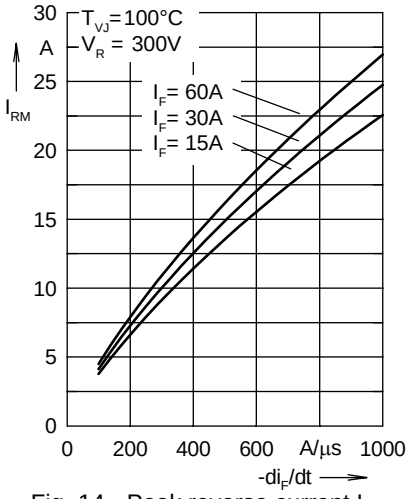


Fig. 14 Peak reverse current I_{RM} versus $-di_F/dt$

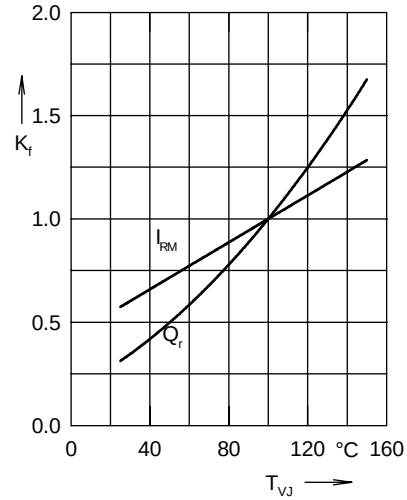


Fig. 15 Dynamic parameters Q_r, I_{RM} versus T_{VJ}

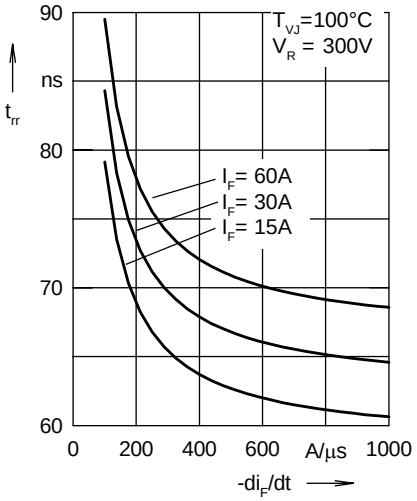


Fig. 16 Recovery time t_{rr} versus $-di_F/dt$

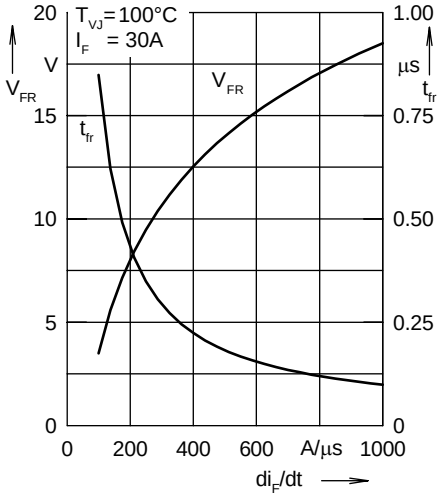


Fig. 17 Peak forward voltage V_{FR} and t_{fr} versus di_F/dt

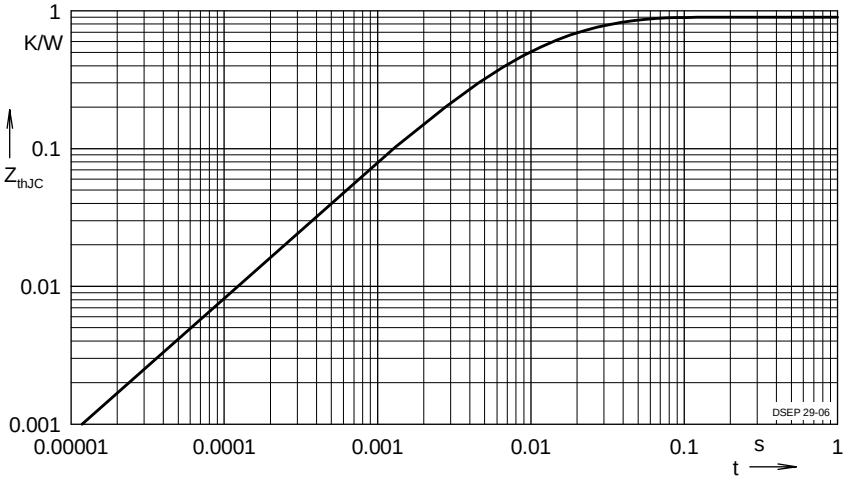


Fig. 18 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.502	0.0052
2	0.193	0.0003
3	0.205	0.0162